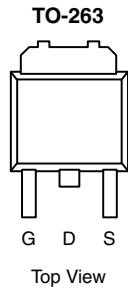


P-Channel 80-V (D-S) MOSFET

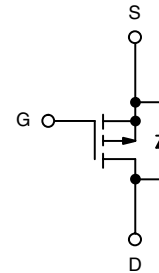
PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A) ^b	Q _g (Typ)
- 80	0.0112 at V _{GS} = - 10 V	- 110	85 nC
	0.0145 at V _{GS} = - 4.5 V	- 109	

FEATURES

- TrenchFET[®] Power MOSFET



Drain Connected to Tab



P-Channel MOSFET

Ordering Information: SUM110P08-11L-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 80	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C	- 110 ^a	A
	T _C = 125 °C	- 71	
	T _A = 25 °C	- 23.5 ^{b, c}	
	T _A = 125 °C	13.6 ^{b, c}	
Pulsed Drain Current	I _{DM}	- 120	
Continuous Source-Drain Diode Current	T _C = 25 °C	- 110	
	T _A = 25 °C	- 9 ^{b, c}	
Avalanche Current	I _{AS}	- 75	
Single-Pulse Avalanche Energy	L = 0.1 mH E _{AS}	281	mJ
Maximum Power Dissipation	T _C = 25 °C	375	W
	T _C = 125 °C	125	
	T _A = 25 °C	13.6 ^{b, c}	
	T _A = 125 °C	4.5 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s R _{thJA}	8	11	°C/W	
Maximum Junction-to-Case (Drain)	Steady State R _{thJC}	0.33	0.4		

Notes:

- Package limited.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 80			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -1\text{ }\mu\text{A}$		- 85		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			- 500	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = -10\text{ V}$	- 120			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		0.0093	0.0112	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -15\text{ A}$		0.012	0.0145	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -20\text{ A}$		85		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		10850		pF
Output Capacitance	C_{oss}			800		
Reverse Transfer Capacitance	C_{rss}			700		
Total Gate Charge	Q_g	$V_{DS} = -40\text{ V}, V_{GS} = -10\text{ V}, I_D = -110\text{ A}$		180	270	nC
				85	130	
Gate-Source Charge	Q_{gs}	$V_{DS} = -40\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -110\text{ A}$		35		
Gate-Drain Charge	Q_{gd}			42		
Gate Resistance	R_g	$f = 1\text{ MHz}$		3.6		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -40\text{ V}, R_L = 0.36\text{ }\Omega$ $I_D \cong -110\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		20	30	ns
Rise Time	t_r			330	500	
Turn-Off Delay Time	$t_{d(off)}$			135	205	
Fall Time	t_f			550	825	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 110	A
Pulse Diode Forward Current ^a	I_{SM}				- 120	
Body Diode Voltage	V_{SD}	$I_S = -20\text{ A}$		- 0.8	- 1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		65	100	ns
Body Diode Reverse Recovery Charge	Q_{rr}			135	205	nC
Reverse Recovery Fall Time	t_a			43		ns
Reverse Recovery Rise Time	t_b			22		

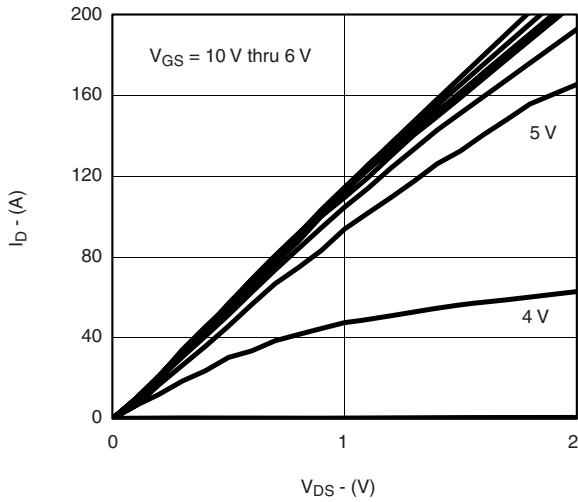
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

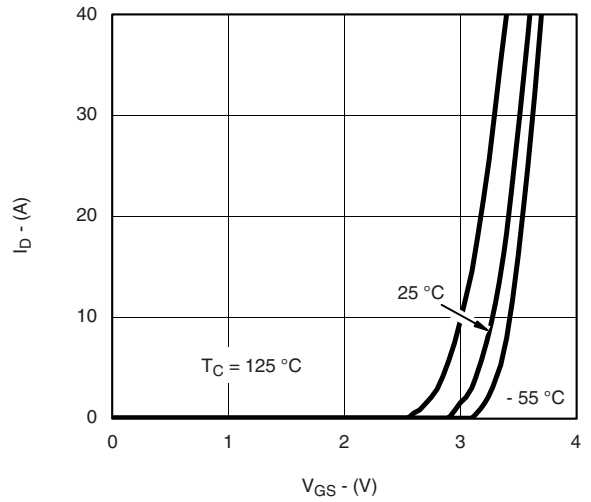
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



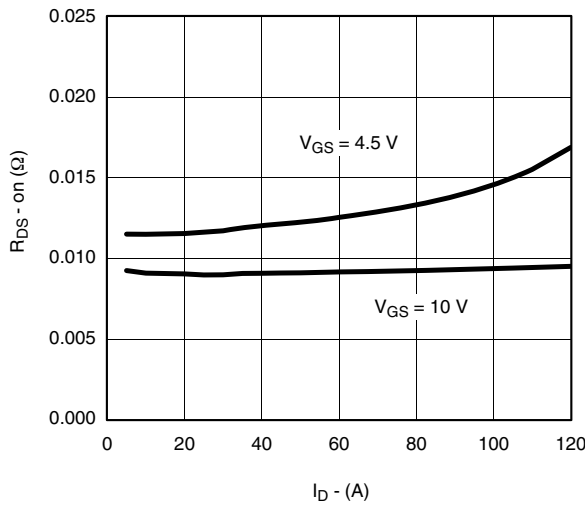
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



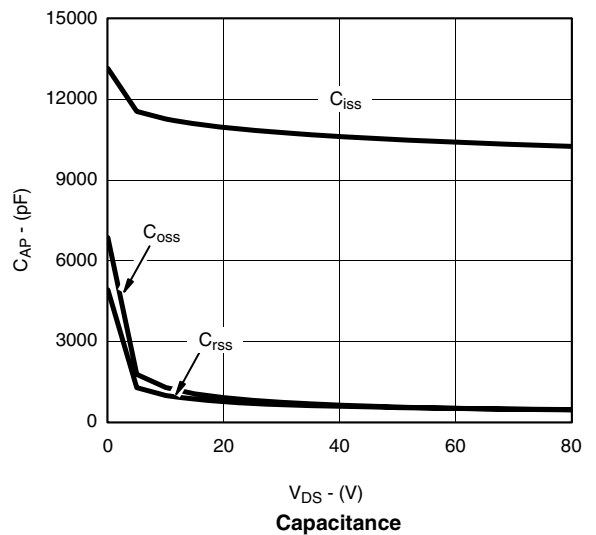
Output Characteristics



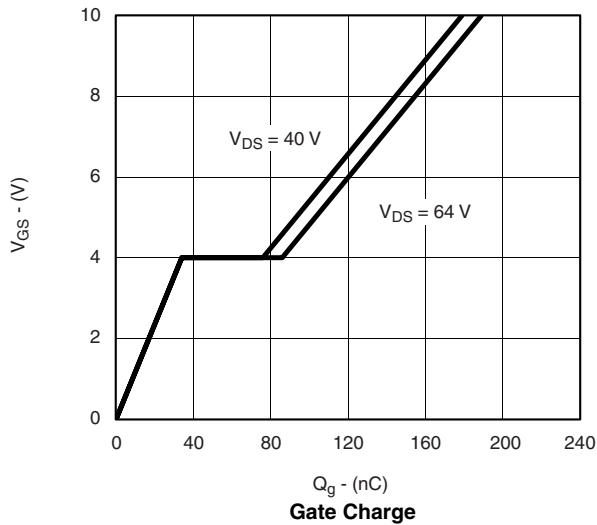
Transfer Characteristics



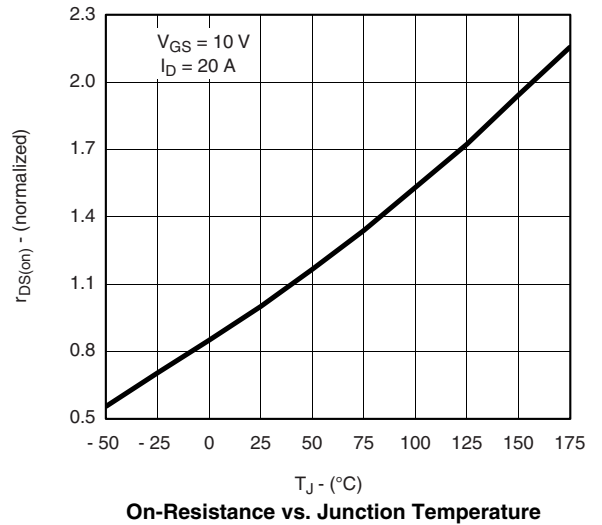
On-Resistance vs. Drain Current



Capacitance



Gate Charge



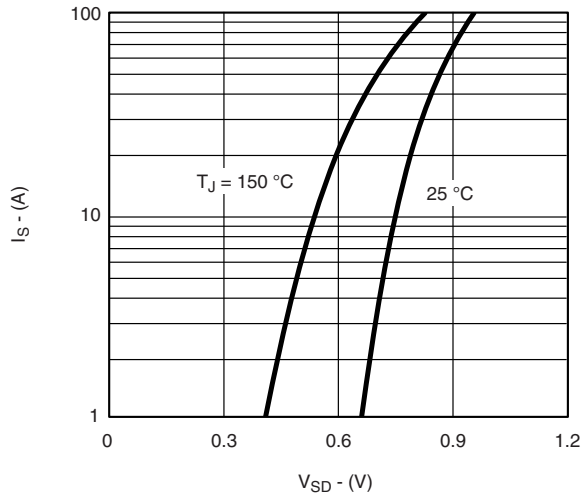
On-Resistance vs. Junction Temperature

SUM110P08-11L

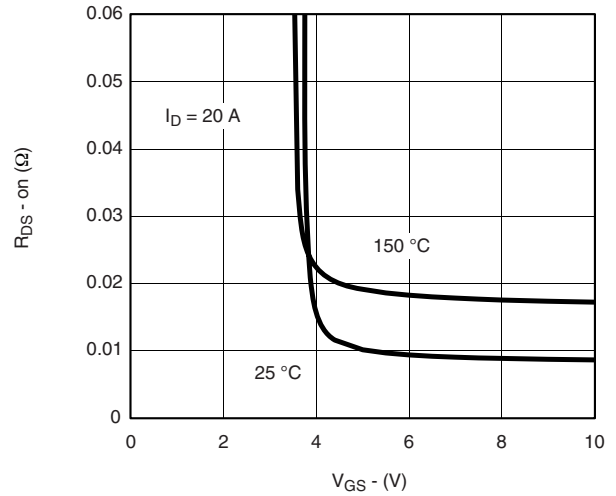


Vishay Siliconix

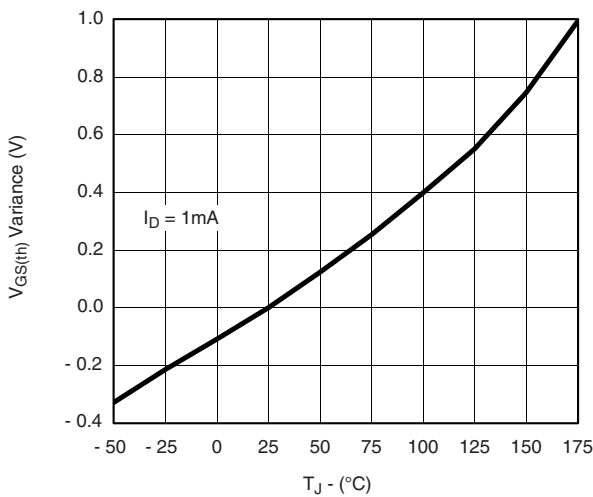
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



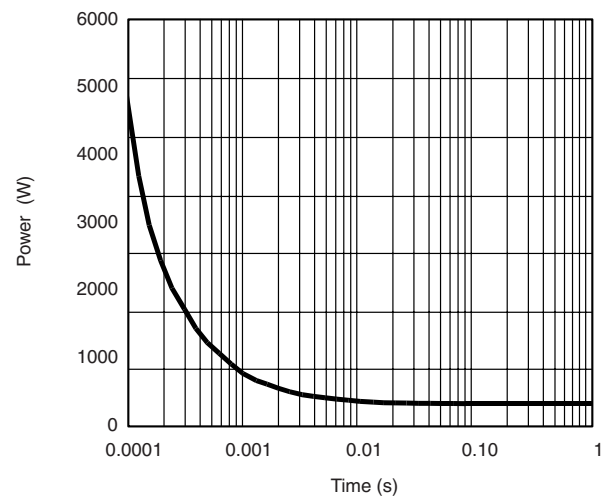
Source-Drain Diode Forward Voltage



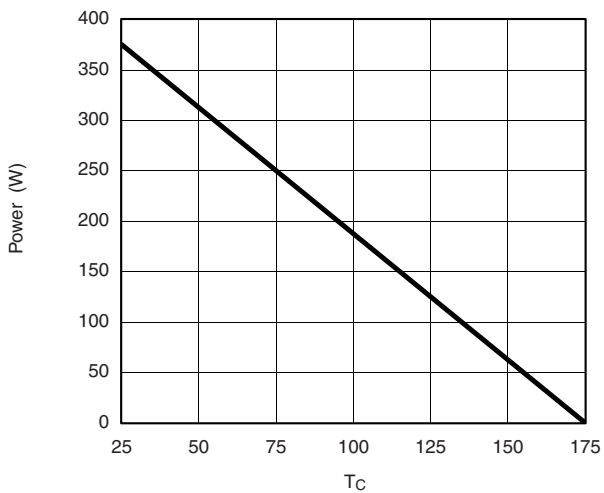
On-Resistance vs. Gate-to-Source Voltage



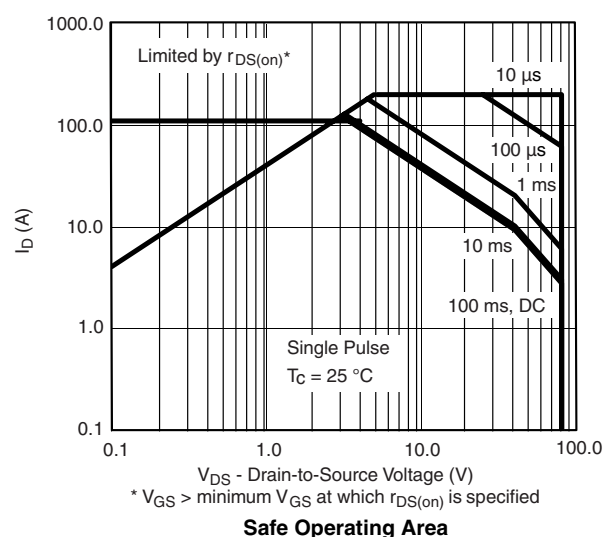
Threshold Voltage



Single Pulse Power, Junction-to-Case ($T_C = 25\text{ °C}$)



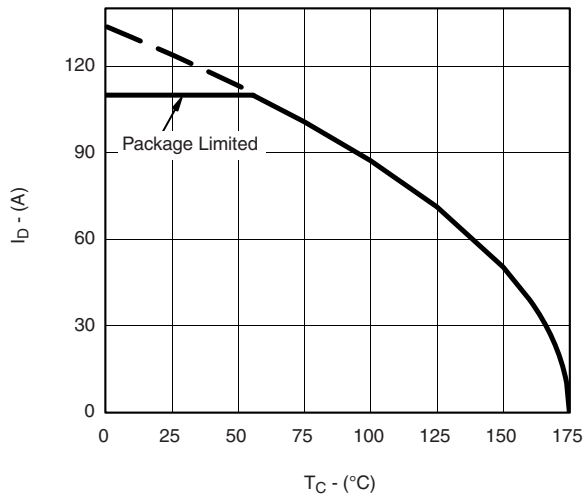
Power Derating, Junction-to-Case



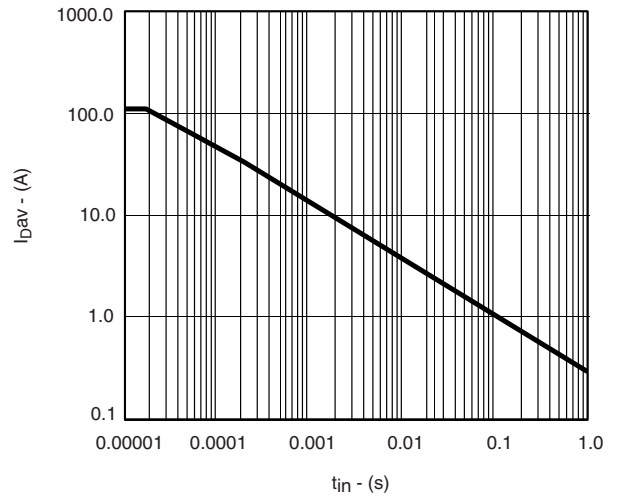
Safe Operating Area



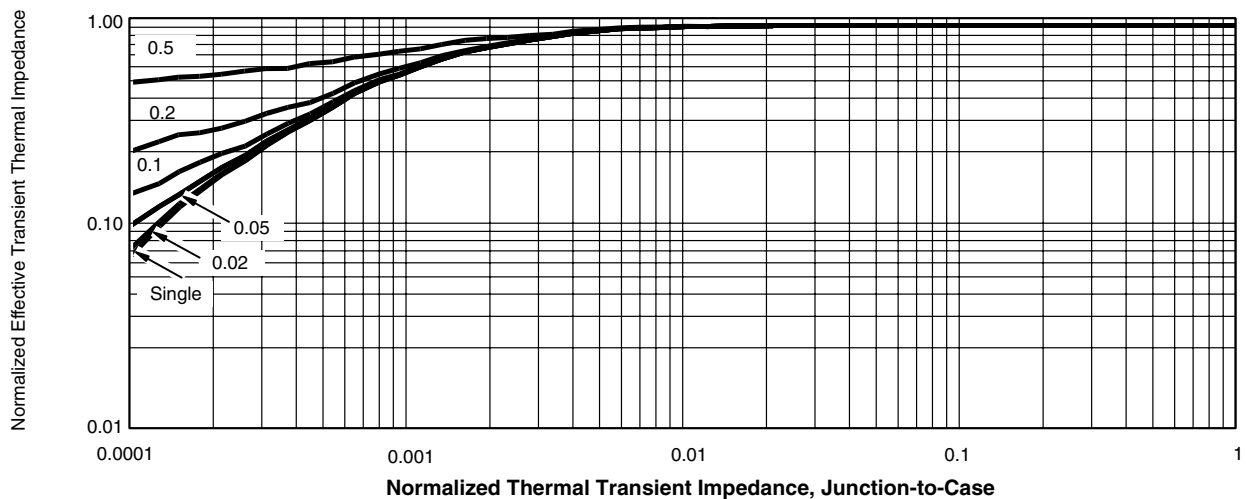
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Max Avalanche and Drain Current vs. Case Temperature



Avalanche Current vs. Time



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?73471>.



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